

**SMPS MOSFET**

**IRFR3711PbF**  
**IRFU3711PbF**

**Applications**

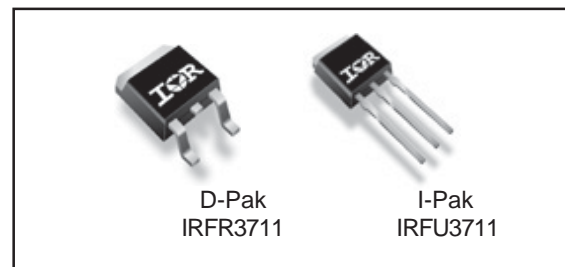
- High Frequency Isolated DC-DC Converters with Synchronous Rectification for Telecom and Industrial Use
- High Frequency Buck Converters for Server Processor Power Synchronous FET
- Optimized for Synchronous Buck Converters Including Capacitive Induced Turn-on Immunity
- 100% R<sub>G</sub> Tested
- Lead-Free

**Benefits**

- Ultra-Low Gate Impedance
- Very Low R<sub>DS(on)</sub> at 4.5V V<sub>GS</sub>
- Fully Characterized Avalanche Voltage and Current

HEXFET® Power MOSFET

V <sub>DSS</sub>	R <sub>DS(on)</sub> max	I <sub>D</sub>
20V	6.5mΩ	110A <sup>④</sup>



**Absolute Maximum Ratings**

Symbol	Parameter	Max	Units
V <sub>DS</sub>	Drain-Source Voltage	20	V
V <sub>GS</sub>	Gate-Source Voltage	± 20	
I <sub>D</sub> @ T <sub>C</sub> = 25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	100 <sup>④</sup>	A
I <sub>D</sub> @ T <sub>C</sub> = 100°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	69 <sup>④</sup>	
I <sub>DM</sub>	Pulsed Drain Current <sup>①</sup>	440	
P <sub>D</sub> @ T <sub>A</sub> = 25°C	Maximum Power Dissipation <sup>⑤</sup>	2.5	W
P <sub>D</sub> @ T <sub>C</sub> = 25°C	Maximum Power Dissipation	120	
	Linear Derating Factor	0.96	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Junction and Storage Temperature Range	-55 to +150	°C

**Thermal Resistance**

Symbol	Parameter	Typ	Max	Units
R <sub>θJC</sub>	Junction-to-Case <sup>⑥</sup>	—	1.04	°C/W
R <sub>θJA</sub>	Junction-to-Ambient (PCB Mount) <sup>⑥⑦</sup>	—	50	
R <sub>θJA</sub>	Junction-to-Ambient <sup>⑥</sup>	—	110	

Notes ① through ⑦ are on page 10

# IRFR/U3711PbF

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Static @  $T_J = 25^\circ\text{C}$  (unless otherwise specified)

Symbol	Parameter	Min	Typ	Max	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	20	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.022	—	V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	5.2	6.5	m $\Omega$	$V_{GS} = 10V, I_D = 15A$ ③
		—	6.7	8.5		$V_{GS} = 4.5V, I_D = 12A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	1.0	—	3.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	140	$\mu A$	$V_{DS} = 20V, V_{GS} = 0V$
		—	—	20		$V_{DS} = 16V, V_{GS} = 0V$
		—	—	100		$V_{DS} = 16V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	200	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-200		$V_{GS} = -20V$

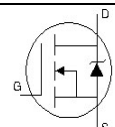
Dynamic @  $T_J = 25^\circ\text{C}$  (unless otherwise specified)

Symbol	Parameter	Min	Typ	Max	Units	Conditions
$g_{fs}$	Forward Transconductance	53	—	—	S	$V_{DS} = 16V, I_D = 30A$
$Q_g$	Total Gate Charge	—	29	44	nC	$I_D = 15A$
$Q_{gs}$	Gate-to-Source Charge	—	7.3	—		$V_{DS} = 10V$
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	8.9	—		$V_{GS} = 4.5V$ ③
$Q_{oss}$	Output Gate Charge	—	33	—		$V_{GS} = 0V, V_{DS} = 10V$
$R_G$	Gate Resistance	0.3	—	2.5	$\Omega$	
$t_{d(on)}$	Turn-On Delay Time	—	12	—	ns	$V_{DD} = 10V$
$t_r$	Rise Time	—	220	—		$I_D = 30A$
$t_{d(off)}$	Turn-Off Delay Time	—	17	—		$R_G = 1.8\Omega$
$t_f$	Fall Time	—	12	—		$V_{GS} = 4.5V$ ③
$C_{iss}$	Input Capacitance	—	2980	—	pF	$V_{GS} = 0V$
$C_{oss}$	Output Capacitance	—	1770	—		$V_{DS} = 10V$
$C_{riss}$	Reverse Transfer Capacitance	—	280	—		$f = 1.0\text{MHz}$

## Avalanche Characteristics

Symbol	Parameter	Typ	Max	Units
$E_{AS}$	Single Pulse Avalanche Energy②	—	460	mJ
$I_{AR}$	Avalanche Current ①	—	30	A

## Diode Characteristics

Symbol	Parameter	Min	Typ	Max	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	110 ④	A	MOSFET symbol showing the integral reverse p-n junction diode. 
$I_{SM}$	Pulsed Source Current (Body Diode) ①	—	—	440		
$V_{SD}$	Diode Forward Voltage	—	0.88	1.3	V	$T_J = 25^\circ\text{C}, I_S = 30A, V_{GS} = 0V$ ③
		—	0.82	—		$T_J = 125^\circ\text{C}, I_S = 30A, V_{GS} = 0V$ ③
$t_{rr}$	Reverse Recovery Time	—	50	75	ns	$T_J = 25^\circ\text{C}, I_F = 16A, V_R = 10V$
$Q_{rr}$	Reverse Recovery Charge	—	61	92	nC	$di/dt = 100A/\mu s$ ③
$t_{rr}$	Reverse Recovery Time	—	48	72	ns	$T_J = 125^\circ\text{C}, I_F = 16A, V_R = 10V$
$Q_{rr}$	Reverse Recovery Charge	—	65	98	nC	$di/dt = 100A/\mu s$ ③

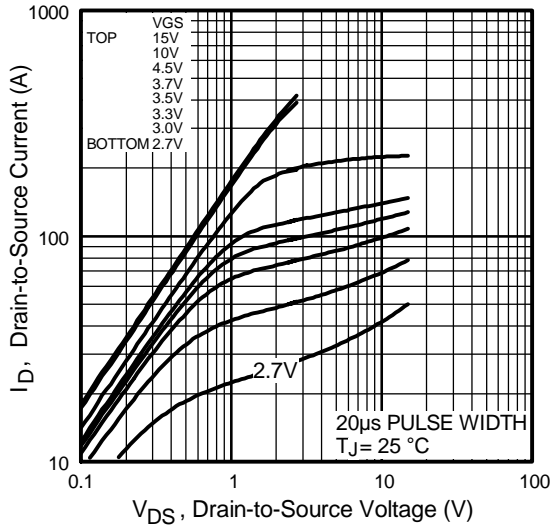


Fig 1. Typical Output Characteristics

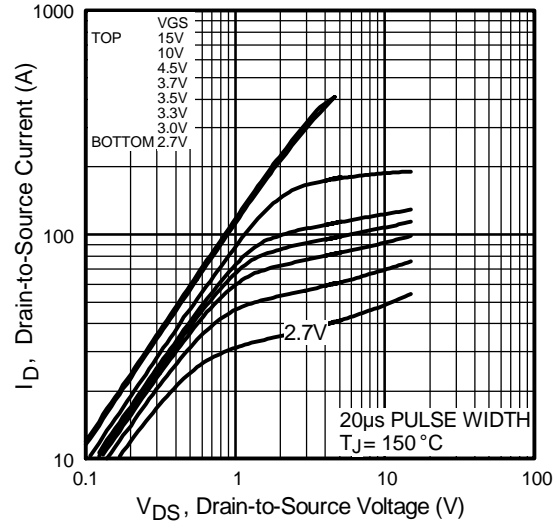


Fig 2. Typical Output Characteristics

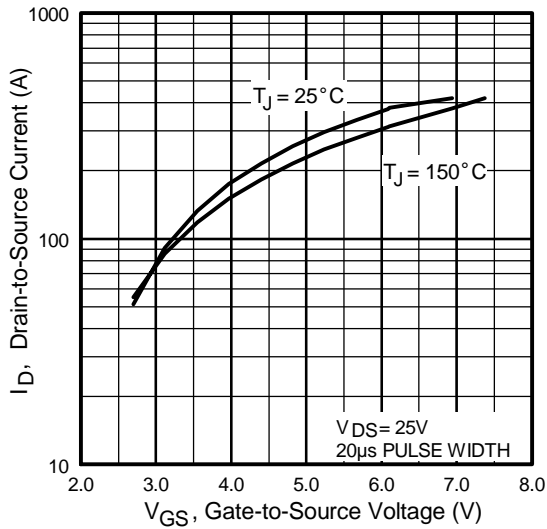


Fig 3. Typical Transfer Characteristics

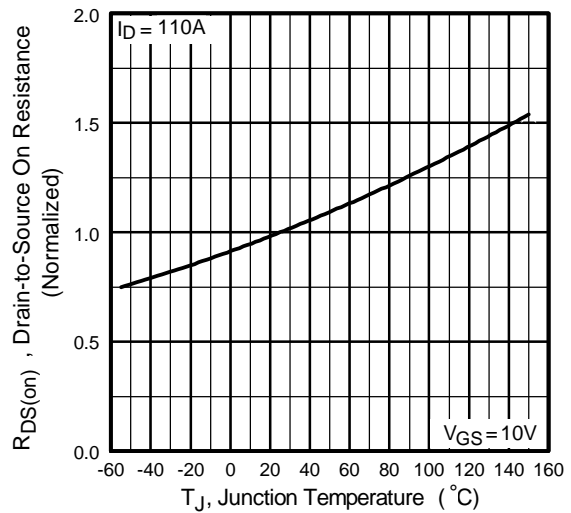
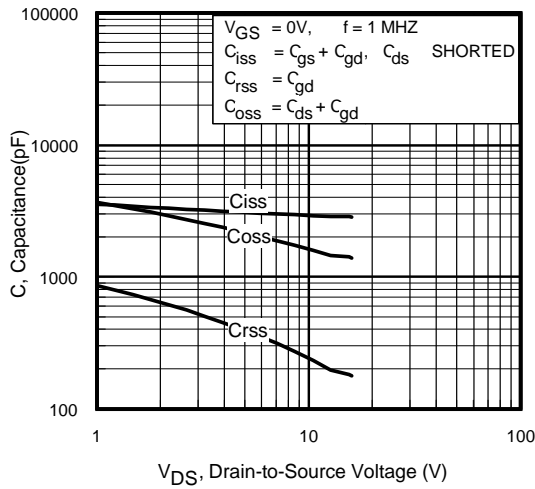
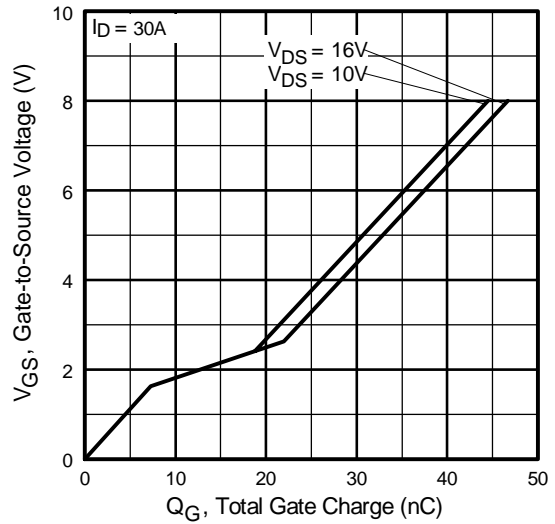


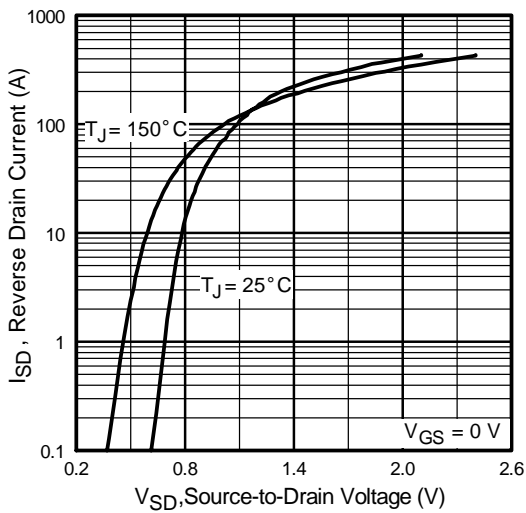
Fig 4. Normalized On-Resistance Vs. Temperature



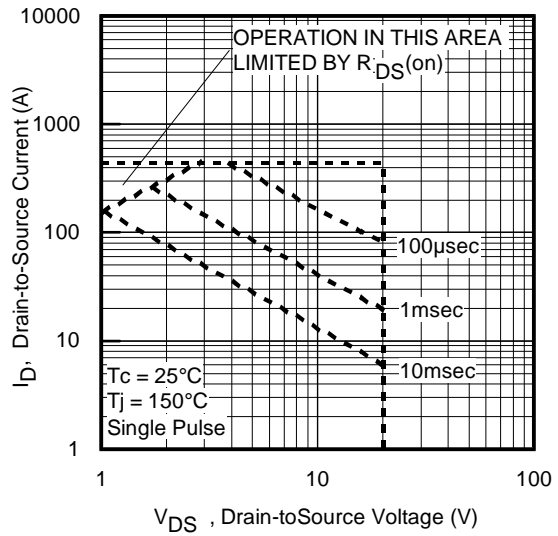
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



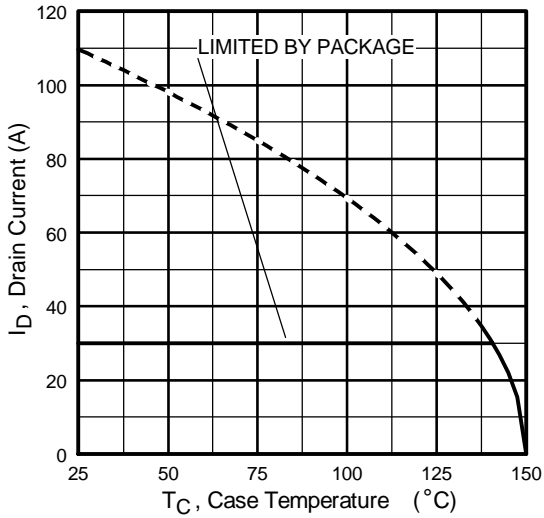
**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



**Fig 7.** Typical Source-Drain Diode Forward Voltage



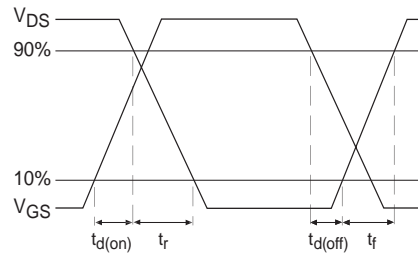
**Fig 8.** Maximum Safe Operating Area



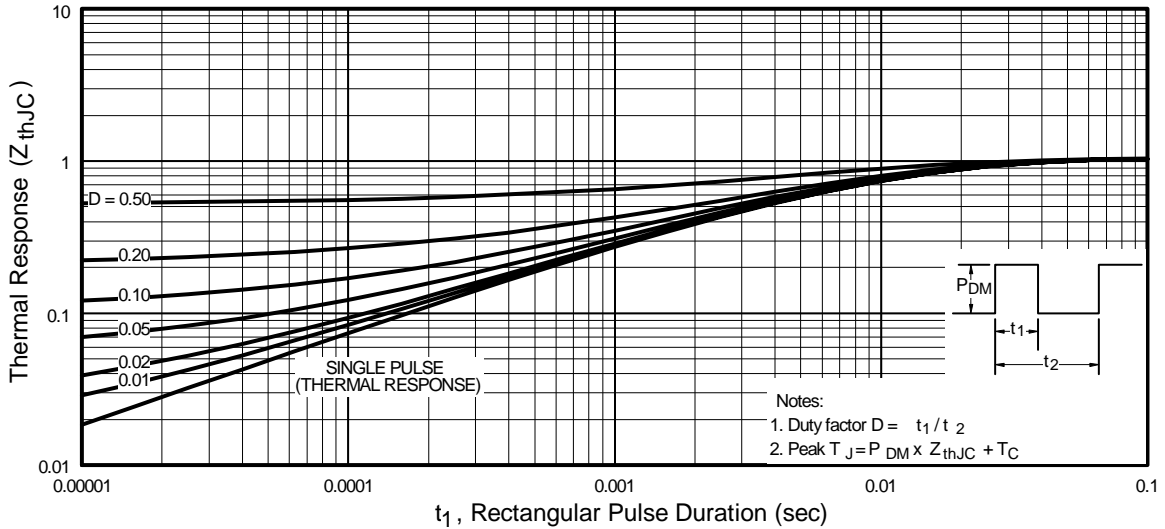
**Fig 9.** Maximum Drain Current Vs. Case Temperature



**Fig 10a.** Switching Time Test Circuit



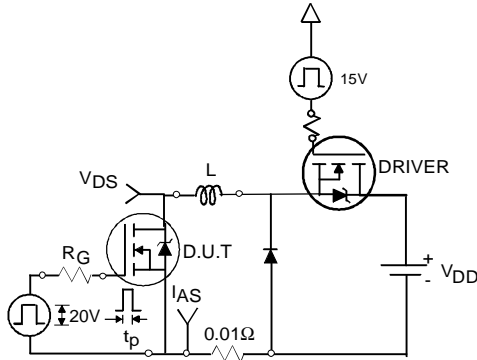
**Fig 10b.** Switching Time Waveforms



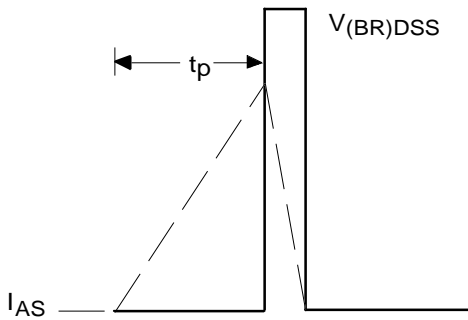
**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case

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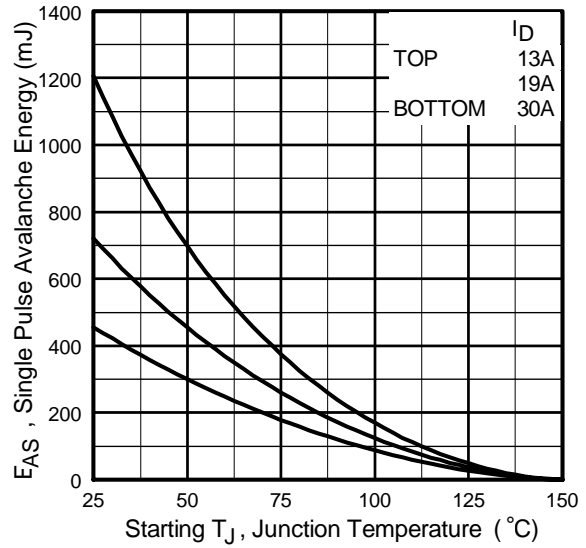
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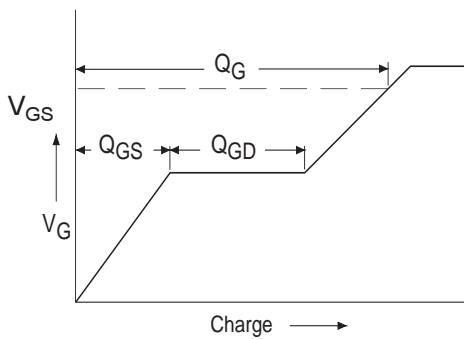
**Fig 12a.** Unclamped Inductive Test Circuit



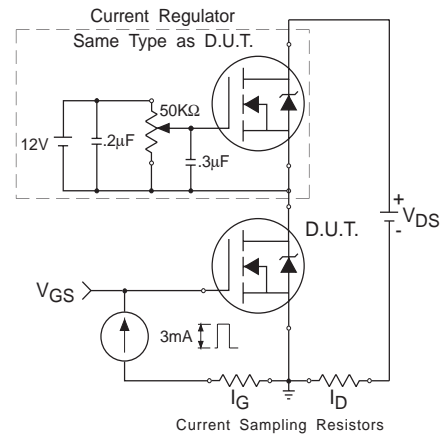
**Fig 12b.** Unclamped Inductive Waveforms



**Fig 12c.** Maximum Avalanche Energy Vs. Drain Current

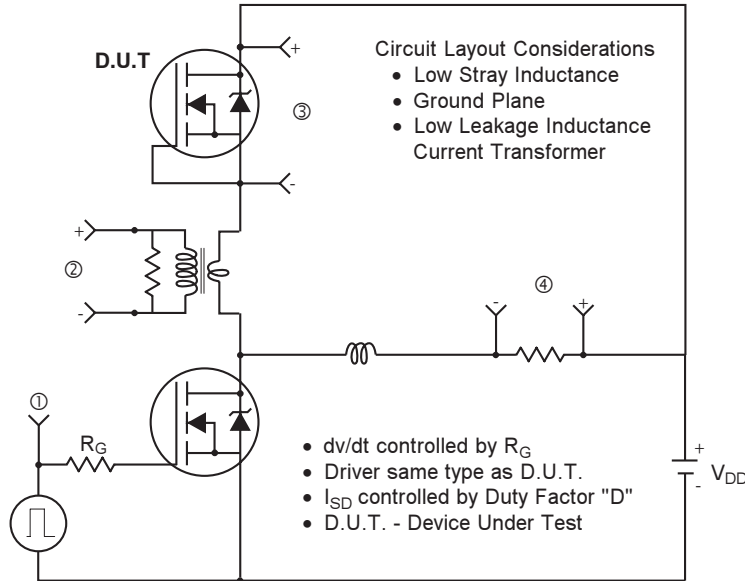


**Fig 13a.** Basic Gate Charge Waveform



**Fig 13b.** Gate Charge Test Circuit

**Peak Diode Recovery dv/dt Test Circuit**



\*  $V_{GS} = 5V$  for Logic Level Devices

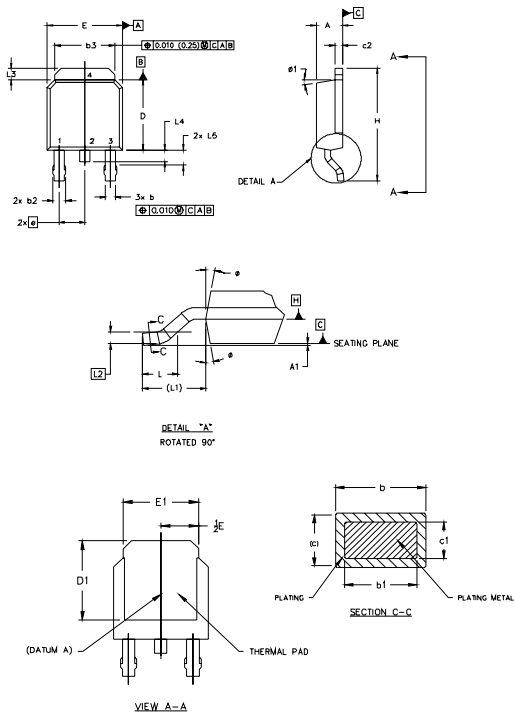
**Fig 14.** For N-Channel HEXFET® Power MOSFETs

# IRFR/U3711PbF

International  
**IR** Rectifier

## D-Pak (TO-252AA) Package Outline

Dimensions are shown in millimeters (inches)



- NOTES:
- 1.0 DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
  - 2.0 DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS].
  - 3.0 LEAD DIMENSION UNCONTROLLED IN L5
  - 4.0 DIMENSION D1 AND E1 ESTABLISH A MINIMUM MOUNTING SURFACE FOR THERMAL PAD.
  - 5.0 SECTION C-C DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN .005 [0.127] AND .010 [0.2540] FROM THE LEAD TIP.
  - 6.0 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
  - 7.0 OUTLINE CONFORMS TO JEDEC OUTLINE TO-252AA.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	.086	.094	
A1		0.13		.005	
b	0.64	0.89	.025	.035	5
b1	0.64	0.79	.025	0.031	5
b2	0.76	1.14	.030	.045	
b3	4.35	5.46	.190	.215	
c	0.46	0.61	.018	.024	5
c1	0.41	0.56	.016	.022	5
c2	.046	0.89	.018	.035	5
D	5.97	6.22	.236	.245	6
D1	5.21	-	.205	-	4
E	6.35	6.73	.250	.265	6
E1	4.52	-	.170	-	4
e	2.29		.090 BSC		
H	9.40	10.41	.370	.410	
L	1.40	1.78	.055	.070	
L1	2.14 REF.		.08 REF.		
L2	0.051 BSC		.020 BSC		
L3	0.89	1.27	.035	.050	
L4		1.02		.040	
L5	1.14	1.52	.045	.060	3
a	0"	10"	0"	10"	
a1	0"	15"	0"	15"	

**LEAD ASSIGNMENTS**

**HEXFET**

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

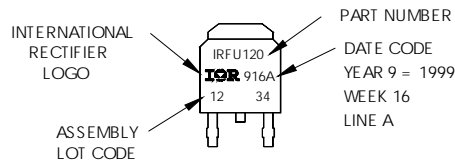
**IGBTs, CoPACK**

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

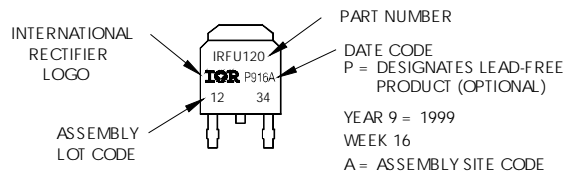
## D-Pak (TO-252AA) Part Marking Information

EXAMPLE: THIS IS AN IRFR120  
WITH ASSEMBLY  
LOT CODE 1234  
ASSEMBLED ON WW 16, 1999  
IN THE ASSEMBLY LINE "A"

Note: "P" in assembly line position  
indicates "Lead-Free"



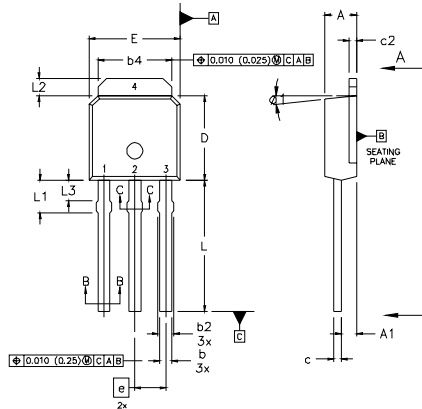
OR





## I-Pak (TO-251AA) Package Outline

Dimensions are shown in millimeters (inches)



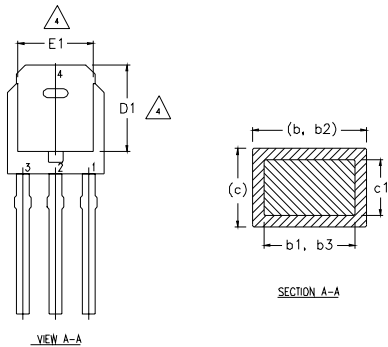
**NOTES:**

- 1 DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
- 2 DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
- 3 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- 4 THERMAL PAD CONTOUR OPTION WITHIN DIMENSION b4, L2, E1 & D1.
- 5 LEAD DIMENSION UNCONTROLLED IN L3.
- 6 DIMENSION b1, b3 APPLY TO BASE METAL ONLY.
- 7 OUTLINE CONFORMS TO JEDEC OUTLINE TO-251AA.
- 8 CONTROLLING DIMENSION : INCHES.

**LEAD ASSIGNMENTS**

**HEXFET**

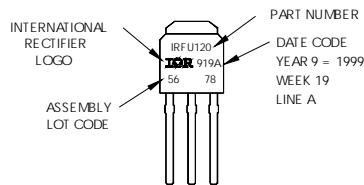
- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN



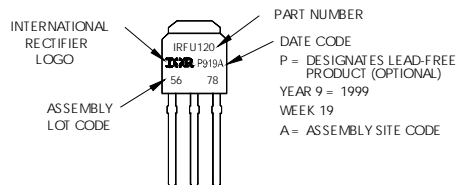
SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	0.086	.094	
A1	0.89	1.14	0.035	0.045	
b	0.64	0.89	0.025	0.035	
b1	0.64	0.79	0.025	0.031	4
b2	0.76	1.14	0.030	0.045	
b3	0.76	1.04	0.030	0.041	4
b4	5.00	5.46	0.195	0.215	
c	0.46	0.61	0.018	0.024	
c1	0.41	0.56	0.016	0.022	
c2	.046	0.86	0.018	0.035	
D	5.97	6.22	0.235	0.245	3, 4
D1	5.21	-	0.205	-	4
E	6.35	6.73	0.250	0.265	3, 4
E1	4.32	-	0.170	-	4
e	2.29		0.090 BSC		
L	8.89	9.60	0.350	0.380	
L1	1.91	2.29	0.075	0.090	
L2	0.89	1.27	0.035	0.050	4
L3	1.14	1.52	0.045	0.060	5
ø1	Ø	15'	Ø	15'	

## I-Pak (TO-251AA) Part Marking Information

EXAMPLE: THIS IS AN IRFU120 WITH ASSEMBLY LOT CODE 5678 ASSEMBLED ON WW 19, 1999 IN THE ASSEMBLY LINE "A"  
**Note:** "P" in assembly line position indicates "Lead-Free"



**OR**

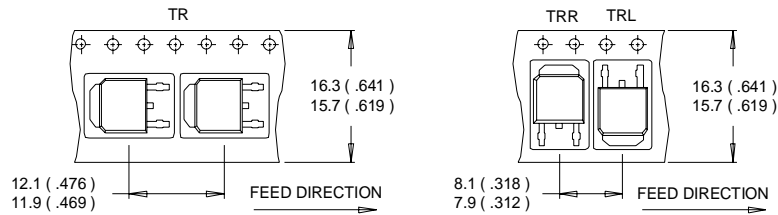


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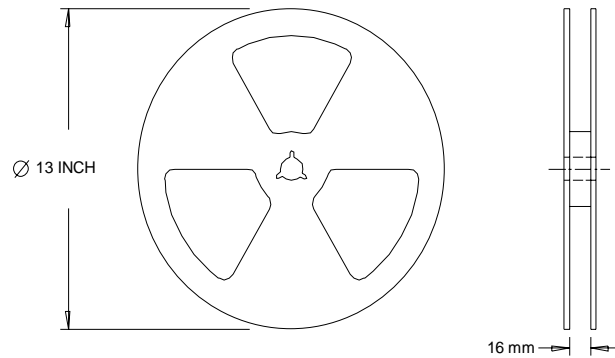
## D-Pak (TO-252AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



**NOTES:**

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS ( INCHES ).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



**NOTES:**

1. OUTLINE CONFORMS TO EIA-481.

**Notes:**

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting  $T_J = 25^\circ\text{C}$ ,  $L = 1.0\text{mH}$   
 $R_G = 25\Omega$ ,  $I_{AS} = 30\text{A}$ .
- ③ Pulse width  $\leq 400\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
- ④ Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 30A.
- ⑤ When mounted on 1" square PCB (FR-4 or G-10 Material) .  
For recommended footprint and soldering techniques refer to application note #AN-994
- ⑥  $R_\theta$  is measured at  $T_J$  approximately at  $90^\circ\text{C}$

Data and specifications subject to change without notice.  
This product has been designed and qualified for the industrial market.  
Qualification Standards can be found on IR's Web site.

International  
**IR** Rectifier

**IR WORLD HEADQUARTERS:** 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105  
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Note: For the most current drawings please refer to the IR website at:  
<http://www.irf.com/package/>

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